Digital Integrated Circuits (83-313)

Lecture 8: Memory Peripherals

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TAs:

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Lecture Content



Memory Peripherals Overview





Memory Architecture



4

<u>Memory Size</u>: W Words of C bits = $W \ge C$ bits <u>Address bus</u>: A bits $\rightarrow W=2^A$

Number of Words in a Row: 2^{M} Multiplexing Factor: M

<u>Number of Rows</u>: 2^{A-M} <u>Number of Columns</u>: $C \ge 2^{M}$

<u>Row Decoder</u>: $A \rightarrow 2^{A-M}$ <u>Column Decoder</u>: $M \rightarrow 2^{M}$



Memory Timing: Definitions



Major Peripheral Circuits

- Row Decoder
- Column Multiplexer
- Sense Amplifier
- Write Driver
- Precharge Circuit



Row Decoder Design





Row Decoders

- A Decoder reduces the number of select signals by log₂.
 - Number of Rows: N
 - Number of Row Address Bits: log_2N





Row Decoders

• Standard Decoder Design:

- Each output row is driven by an AND gate with $k = \log_2 N$ inputs.
- Each gate has a unique combination of address inputs (or their inverted values).
- For example, an 8-bit row address has 256 8-input AND gates, such as:

$$WL_0 = \overline{A}_7 \overline{A}_6 \overline{A}_5 \overline{A}_4 \overline{A}_3 \overline{A}_2 \overline{A}_1 \overline{A}_0$$

$$WL_{255} = A_7 A_6 A_5 A_4 A_3 A_2 A_1 A_0$$

• NOR Decoder:

- DeMorgan will provide us with a NOR Decoder.
- In the previous example, we'll get 256 8-input NOR gates:

$$WL_{0} = A_{7} + A_{6} + A_{5} + A_{4} + A_{3} + A_{2} + A_{1} + A_{0}$$
$$WL_{255} = \overline{\overline{A}}_{7} + \overline{\overline{A}}_{6} + \overline{\overline{A}}_{5} + \overline{\overline{A}}_{4} + \overline{\overline{A}}_{3} + \overline{\overline{A}}_{2} + \overline{\overline{A}}_{1} + \overline{\overline{A}}_{0}$$



How should we build it?

- Let's build a row decoder for a 256x256 SRAM Array.
 - We need 256 8-input AND Gates.
 - Each gate drives 256 bitcells
- We have various options:













Reminder: Logical Effort

$$t_{pd,i} = t_{pINV} \left(p_i \gamma + EF_i \right)$$

$$EF_i \triangleq LE_i \cdot f_i = LE_i \cdot \frac{b_i \cdot C_{in,i+1}}{C_{in,i}} \qquad PE = F \cdot \prod LE \cdot B = \frac{C_L}{C_{in,1}} \cdot \prod LE_i \prod b_i$$

$$EF_{opt} = \sqrt[N]{PE} = \sqrt[N]{F \cdot \prod LE_i \prod b_i}$$

$$N_{opt} = \log_{EF_{opt}} PE = \log_{EF_{opt}} F \cdot LE \cdot B$$

$$t_{pd} = t_{pINV} \sum \left(p_i \gamma + EF_i \right) = t_{pINV} \left(\gamma \sum p_i + N \cdot \sqrt[N]{PE} \right)$$



Problem Setup

• For LE calculation we need to start with:

- Output Load (C_L)
- Input Capacitance (C_{in})
- Branching (B)
- What is the Load Capacitance?
 - 256 bitcells on each Word Line $C_{WL} = 256 \cdot C_{Cell} + C_{Wire}$
 - Let's ignore the wire for now...

• What is the Input Capacitance?

• Let's assume our address drivers can drive a bit more than a bitcell, so:



 $C_{in,addr_driver} = 4 \cdot C_{Cell}$

Problem Setup

- What is the Branching Effort?
 - Lets take another look at the Boolean expressions:





- We see that half of the signals use A_i and half use A_i !
- So each address driver drives 128 8-input AND gates, but only one is on the selected WL path.

$$C_{on path} = C_{nand}; \quad C_{off path} = 127 \cdot C_{nand}$$
$$B_{add_driver} = \frac{C_{on path} + C_{off path}}{C_{on path}} = \frac{C_{nand} + 127 \cdot C_{nand}}{C_{nand}} = 128$$



Number of Stages

- Altogether the path effort is: $PE = LE \cdot B \cdot F = LE \cdot \Pi b_i \frac{C_{WL}}{C_{address}} = LE \cdot 128 \cdot \frac{256C_{Cell}}{4C_{Cell}}$
 - $= LE \cdot 8k = 2^{13} \cdot LE$

• The best case logical effort is $\prod LE = 1$

• So the minimum number of *PE* stages for optimal delay is:

$$PE = 2^{13}$$
$$N_{opt} = \log_{3.6} 2^{13} = 7$$

That's a lot of stages!



So which implementation should we use?

• The one with the minimum Logical Effort:





New optimal number of Stages

• So now we can calculate the actual path effort:

$$PE = F \cdot \Pi b_i \cdot \Pi LE_i =$$

= 2.37 \cdot 2^{13} = 19.418k
 $N_{opt} = \log_{3.6} PE = 7.7$



• We could add another inverter or two to get closer to the optimal number of stages...



Implementation Problems

Address Line Capacitance:

- Our assumption was that $C_{\text{in,addr_driver}} = 4C_{\text{cell}}$.
- But each address drives 128 gates
 - That's a really long wire with high capacitance.
- This means that we will need to buffer the address lines
 - This will probably ruin our whole analysis...

• Bit-cell Pitch:

- Each signal drives one row of bitcells.
- How will we fit 8 address signals into this pitch?



Predecoding - Concept

• Solution:

• Let's look at two decoder paths: WL₂₅₄, WL₂₅₅



- We see that there are many "shared" gates.
 - So why not share them?
- For instance, we can use the purple output for both gates...

Predecoding - Method

• How do we do this?

- If we look at the final Boolean expression, it has combinations of groups of inputs.
- By grouping together a few inputs, we actually create a small decoder.
- Then we just AND the outputs of all the "pre" decoders.
- For example: Two 4:16 predecoders

$$D = dec(A_0, A_1, A_2, A_3); E = dec(A_4, A_5, A_6, A_7);$$

$$WL_0 = D_0 \cdot E_0; WL_{255} = D_{15} \cdot E_{15}; WL_{254} = D_{15} \cdot E_{14};$$



Predecoding - Example

• Let's look at our example:

$$WL_{0} = D_{0} \cdot E_{0}$$
$$D = dec(A_{0}, A_{1}, A_{2}, A_{3}) \qquad WL_{255} = D_{15} \cdot E_{15}$$
$$E = dec(A_{4}, A_{5}, A_{6}, A_{7}) \qquad WL_{254} = D_{15} \cdot E_{14}$$

- What is our new branching effort?
 - As before, each address drives half the lines of the small decoder.
 - Each predecoder output drives 256/16 post-decoder gates.
 - Altogether, the branching effort is:

$$B = b_{addr_driver} \cdot b_{predecoder} = \frac{16}{2} \cdot \frac{256}{16} = 128$$

• Same as before!



Predecoding - Solution

• Why is this a better solution?

- Each Address driver is only driving four gates
 - less capacitance.
- We saved a ton of area by "sharing" gates.
- We can "Pitch Fit" 2-input NAND gates.



Another Predecoding Example

- We can try using four 2-input predecoders:
 - This will require us to use 256 4-input NAND gates.



How do we choose a configuration?

- <u>Pitch Fitting</u>: 2-input NANDs vs. 4-input NAND.
- <u>Switching Capacitance</u>: How many wires switch at each transition?
- **<u>Stages Before the large cap</u>**: Distribution of the load along the delay.
- <u>Conclusion</u>: Usually do as much predecoding as possible!



Alternative Solution: Dynamic Decoders



2-input NOR decoder



Column Multiplexer





Column Multiplexer

• First option – PTL Mux with decoder

- Fast only 1 transistor in signal path.
- Large transistor Count





CS



4 to 1 tree decoder

- Second option Tree Decoder
 - For 2k:1 Mux, it uses k series transistors.
 - Delay increases quadratically
 - No external decode logic \rightarrow big area reduction.







Precharge and Sense Amp





Precharge Circuitry

Precharge bitlines high before reads





• Equalize bitlines to minimize voltage difference when using sense amplifiers





Sense Amplifiers





Idea: Use Sense Amplifer





Differential Sense Amplifier

- Non-clocked Sense Amp has high static power.
- Clocked sense amp saves power
- Requires <u>sense_clk</u> after enough bitline swing
- Isolation transistors cut off large bitline capacitance







Further Reading

- Rabaey, et al. "Digital Integrated Circuits" (2nd Edition)
- Elad Alon, Berkeley ee141 (online)
- Weste, Harris, "CMOS VLSI Design (4th Edition)"

